

Table 1: General Features

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW26NM50	500 V	< 0.120 Ω	30 A

- TYPICAL R_{DS(on)} = 0.10 Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- IMPROVED ESD CAPABILITY
- LOW INPUT CAPACITANCE AND GATE CHARGE

DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

Figure 1: Package

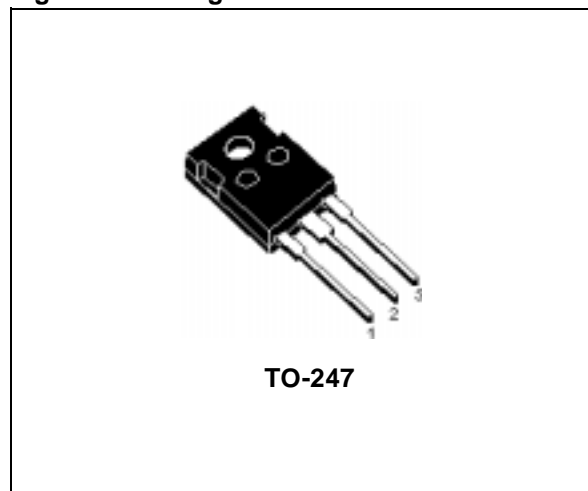


Figure 2: Internal Schematic Diagram

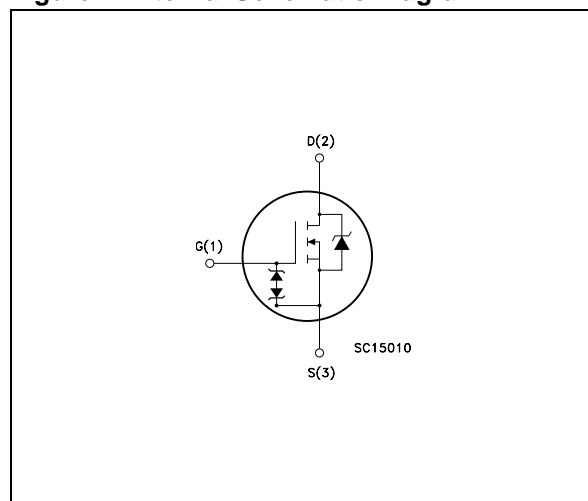


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STW26NM50	W26NM50	TO-247	TUBE

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage ($V_{GS} = 0$)	500	V
V_{DGR}	Drain-gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	500	V
V_{GS}	Gate- source Voltage	± 30	V
I_D	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	30	A
I_D	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	18.9	A
$I_{DM}(\bullet)$	Drain Current (pulsed)	120	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ\text{C}$	313	W
	Derating Factor	2.5	W/ $^\circ\text{C}$
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5K Ω)	6000	V
$dv/dt(1)$	Peak Diode Recovery voltage slope	15	V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150	$^\circ\text{C}$

(\bullet) Pulse width limited by safe operating area

(1) $I_{SD} \leq 26\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.

Table 4: Thermal Data

Rthj-case	Thermal Resistance Junction-case Max	0.4	$^\circ\text{C}/\text{W}$
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum Lead Temperature For Soldering Purpose	300	$^\circ\text{C}$

Table 5: Avalanche Characteristics

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	13	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	740	mJ

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED)

Table 6: Gate-Source Zener Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	$I_{gss} = \pm 1\text{mA}$ (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

Table 7: On /Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \text{ mA}$, $V_{GS} = 0$	500			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$, $T_C = 125^\circ\text{C}$			10 100	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 13 \text{ A}$		0.10	0.12	Ω

Table 8: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (1)$	Forward Transconductance	$V_{DS} = 15 \text{ V}$, $I_D = 13 \text{ A}$		20		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$, $V_{GS} = 0$		3000 700 50		pF pF pF
$C_{oss \text{ eq}} (3)$	Equivalent Output Capacitance	$V_{GS} = 0 \text{ V}$, $V_{DS} = 0 \text{ to } 400 \text{ V}$		300		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on Delay Time Rise Time Turn-off-Delay Time Fall Time	$V_{DD} = 250 \text{ V}$, $I_D = 13 \text{ A}$, $R_G = 4.7 \Omega$, $V_{GS} = 10 \text{ V}$ (see Figure 15)		28 15 13 19		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 400 \text{ V}$, $I_D = 26 \text{ A}$, $V_{GS} = 10 \text{ V}$ (see Figure 18)		76 20 36	106	nC nC nC

Table 9: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (2)$	Source-drain Current Source-drain Current (pulsed)				26 104	A A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 26 \text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 26 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 100\text{V}$ (see Figure 16)		400 5.5 27.8		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 26 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 100\text{V}$, $T_j = 150^\circ\text{C}$ (see Figure 16)		492 7 28.8		ns μC A

(1) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(2) Pulse width limited by safe operating area.

(3) $C_{oss \text{ eq}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .